



#### 80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max       | I <sub>D</sub> Max<br>T <sub>C</sub> = +25°C |
|-------------------|-------------------------------|--|
|                   | 7mΩ @ V <sub>GS</sub> = 10V   | 68A  |
| 80V               | 10.5mΩ @ V <sub>GS</sub> = 6V | 56A  |

### **Description**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

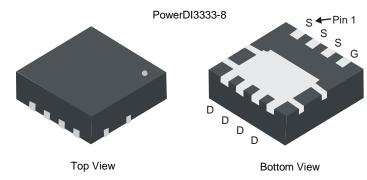
### **Features and Benefits**

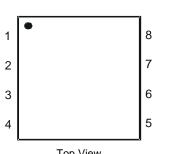
- Rated to +175°C Ideal for High Ambient Temperature Environments
- Low Rds(ON) Ensures On-State Losses are Minimized
- Excellent Q<sub>gd</sub> × R<sub>DS(ON)</sub> Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH8008SFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

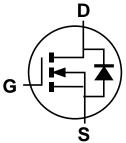
https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)







Top View Pin-Out

**Equivalent Circuit** 

#### Ordering Information (Note 4)

| Part Number     | Case          | Packaging         |
|-----------------|---------------|-------------------|
| DMTH8008SFGQ-7  | PowerDI3333-8 | 2,000/Tape & Reel |
| DMTH8008SFGQ-13 | PowerDI3333-8 | 3,000/Tape & Reel |

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



HZ8 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)

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### **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

| Characteristic  | Symbol                            | Value  | Unit     |   |
|---|-----------------------------------|--------|----------|---|
| Drain-Source Voltage  | VDSS                              | 80     | V        |   |
| Gate-Source Voltage   | $V_{GSS}$                         | ±20    | V        |   |
| Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V                                     | $T_C = +25$ °C<br>$T_C = +100$ °C | lD     | 68<br>48 | А |
| Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$ |                                   | lo     | 17<br>12 | А |
| Maximum Continuous Body Diode Forward Current (Note 6)                                      | Is                                | 68     | Α        |   |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)  | I <sub>DM</sub>                   | 272    | Α        |   |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle =                                 | I <sub>SM</sub>                   | 272    | Α        |   |
| Avalanche Current, L = 1mH (Note 8)   | las                               | 18.7   | Α        |   |
| Avalanche Energy, L = 1mH (Note 8)  | Eas                               | 174.85 | mJ       |   |

### **Thermal Characteristics**

| Characteristic                                   | Symbol                 | Value               | Unit        |      |
|--|------------------------|---------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | T <sub>A</sub> = +25°C | $P_{D}$             | 1.2         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State           | $R_{	heta JA}$      | 125         | °C/W |
| Total Power Dissipation (Note 6)                 | T <sub>A</sub> = +25°C | PD                  | 3.2         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State           | $R_{	hetaJA}$       | 46          | °C/W |
| Total Power Dissipation (Note 7)                 | T <sub>C</sub> = +25°C | PD                  | 50          | W    |
| Thermal Resistance, Junction to Case (Note 7)    |                        | Rелс                | 3.0         | °C/W |
| Operating and Storage Temperature Range          |                        | $T_{J}$ , $T_{STG}$ | -55 to +175 | °C   |

### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

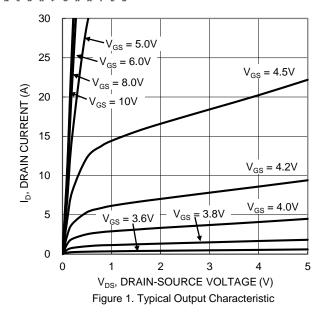
| Characteristic                            | Symbol            | Min | Тур  | Max  | Unit                         | Test Condition   |  |
|---|-------------------|-----|------|------|------------------------------|--|--|
| OFF CHARACTERISTICS (Note 9)              |                   |     |      |      |                              |  |  |
| Drain-Source Breakdown Voltage            | BVDSS             | 80  | _    | _    | $V = V_{GS} = 0V, I_D = 1mA$ |  |  |
| Zero Gate Voltage Drain Current           | IDSS              | -   | _    | 1    | μΑ                           | V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V                  |  |
| Gate-Source Leakage                       | I <sub>GSS</sub>  | -   | _    | ±100 | nA                           | $V_{GS} = \pm 20V, V_{DS} = 0V$                              |  |
| ON CHARACTERISTICS (Note 9)               |                   |     |      |      |                              |  |  |
| Gate Threshold Voltage                    | Vgs(TH)           | 2   | _    | 4    | V                            | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA     |  |
| Static Drain-Source On-Resistance         |                   | -   | 5.0  | 7    | mΩ                           | Vgs = 10V, ID = 14A  |  |
| Static Drain-Source On-Resistance         | RDS(ON)           | _   | 7.1  | 10.5 |                              | V <sub>G</sub> S = 6V, I <sub>D</sub> = 12A                  |  |
| Diode Forward Voltage                     | $V_{SD}$          | _   | 0.8  | 1.2  | V                            | V <sub>GS</sub> = 0V, I <sub>S</sub> = 14A                   |  |
| DYNAMIC CHARACTERISTICS (Note 10)         | ŭ 1 1 1 1 1 1 1 1 |     |      |      |                              |  |  |
| Input Capacitance                         | Ciss              |     | 1945 |      |                              | V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V,<br>f = 1MHz     |  |
| Output Capacitance                        | Coss              | -   | 750  | _    | pF                           |  |  |
| Reverse Transfer Capacitance              | Crss              | -   | 45.8 | _    |                              |  |  |
| Gate Resistance                           | Rg                | _   | 1.8  | _    | Ω                            | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$                   |  |
| Total Gate Charge (V <sub>GS</sub> = 5V)  | Qg                | -   | 18.4 | _    |                              |  |  |
| Total Gate Charge (V <sub>GS</sub> = 10V) | Qg                | _   | 31.7 | _    | nC Vps = 40V, lp = 14A       |  |  |
| Gate-Source Charge                        | $Q_{gs}$          | -   | 8.3  | _    | ПС                           | $V_{DS} = 40V, I_{D} = 14A$                                  |  |
| Gate-Drain Charge                         | $Q_{gd}$          | -   | 8.6  | _    |                              |  |  |
| Turn-On Delay Time                        | tD(ON)            | _   | 9.2  | _    |                              | $V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 14A, R_{G} = 6\Omega$ |  |
| Turn-On Rise Time                         | t <sub>R</sub>    | -   | 11.8 | -    | 20                           |  |  |
| Turn-Off Delay Time                       | tD(OFF)           | _   | 27.0 | _    | ns                           |  |  |
| Turn-Off Fall Time                        | tF                |     | 17.3 | _    |                              |  |  |
| Body Diode Reverse Recovery Time          | trr               |     | 40.6 | _    | ns                           | 1 440 41/44 4000///-   |  |
| Body Diode Reverse Recovery Charge        | Q <sub>RR</sub>   | _   | 50.9 | _    | nC                           | I <sub>S</sub> = 14A, di/dt = 100A/μs                        |  |

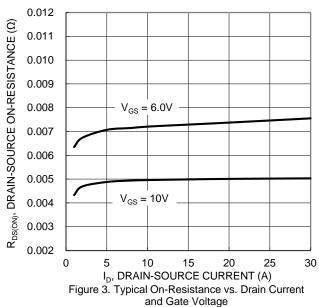
Notes:

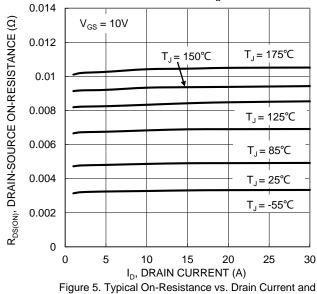
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.











Temperature

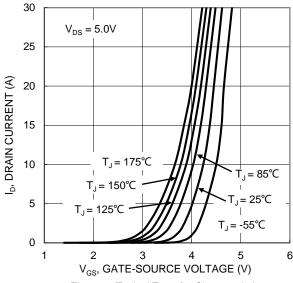
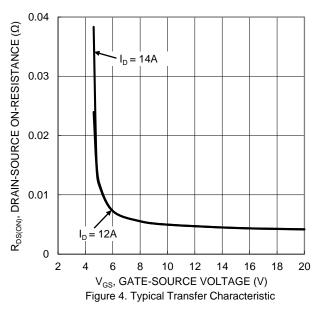


Figure 2. Typical Transfer Characteristic



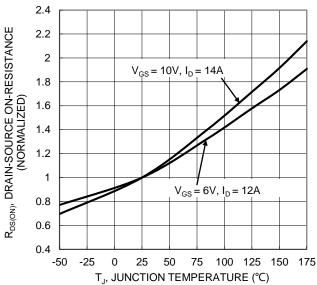


Figure 6. On-Resistance Variation with Temperature



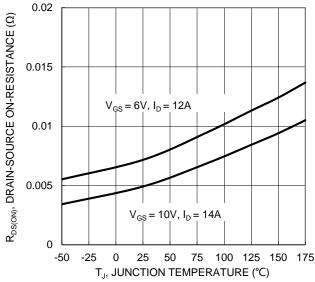


Figure 7. On-Resistance Variation with Temperature

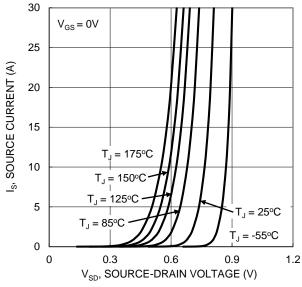


Figure 9. Diode Forward Voltage vs. Current

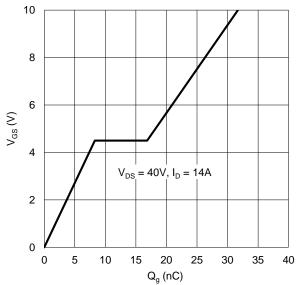


Figure 11. Gate Charge

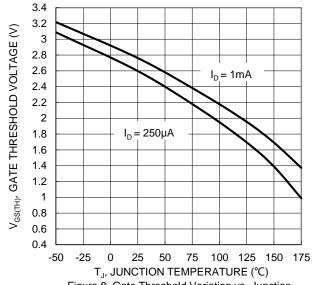
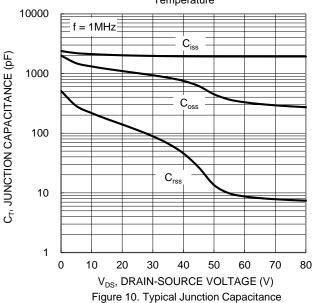


Figure 8. Gate Threshold Variation vs. Junction Temperature



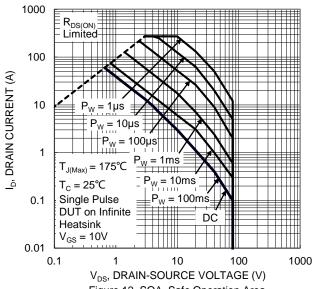


Figure 12. SOA, Safe Operation Area



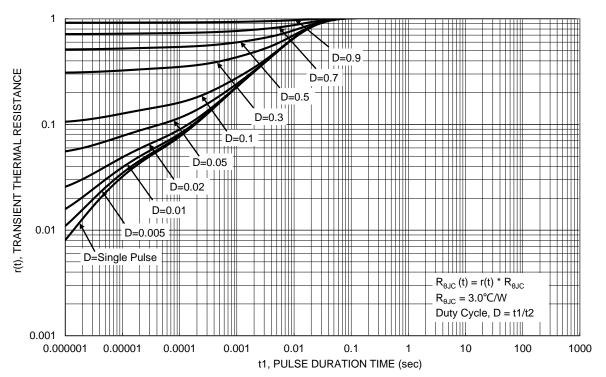


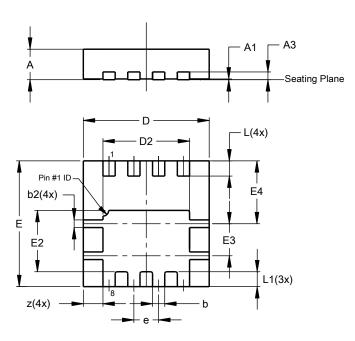
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8

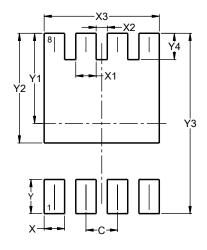


| PowerDI3333-8        |      |      |       |  |  |
|----------------------|------|------|-------|--|--|
| Dim                  | Min  | Max  | Тур   |  |  |
| Α                    | 0.75 | 0.85 | 0.80  |  |  |
| A1                   | 0.00 | 0.05 | 0.02  |  |  |
| A3                   | _    | _    | 0.203 |  |  |
| b                    | 0.27 | 0.37 | 0.32  |  |  |
| b2                   | 0.15 | 0.25 | 0.20  |  |  |
| D                    | 3.25 | 3.35 | 3.30  |  |  |
| D2                   | 2.22 | 2.32 | 2.27  |  |  |
| Е                    | 3.25 | 3.35 | 3.30  |  |  |
| E2                   | 1.56 | 1.66 | 1.61  |  |  |
| E3                   | 0.79 | 0.89 | 0.84  |  |  |
| E4                   | 1.60 | 1.70 | 1.65  |  |  |
| е                    | -    | _    | 0.65  |  |  |
| L                    | 0.35 | 0.45 | 0.40  |  |  |
| L1                   | _    | _    | 0.39  |  |  |
| z                    | _    | _    | 0.515 |  |  |
| All Dimensions in mm |      |      |       |  |  |

# **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for the latest version.$ 

#### PowerDI3333-8



| Dimensions | Value (in mm) |  |  |
|------------|---------------|--|--|
| С          | 0.650         |  |  |
| Χ          | 0.420         |  |  |
| X1         | 0.420         |  |  |
| X2         | 0.230         |  |  |
| Х3         | 2.370         |  |  |
| Υ          | 0.700         |  |  |
| Y1         | 1.850         |  |  |
| Y2         | 2.250         |  |  |
| Y3         | 3.700         |  |  |
| Y4         | 0.540         |  |  |



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DMTH8008SFGQ
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